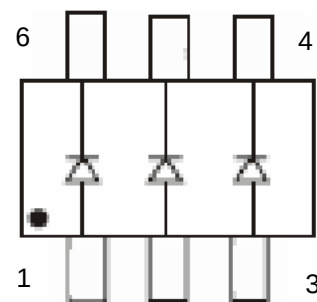


Plastic-Encapsulate Transistors SCHOTTKY BARRIER DIODE ARRAYS

FEATURES

- Low Forward voltage drop
- Fast switching

MARKING:K43



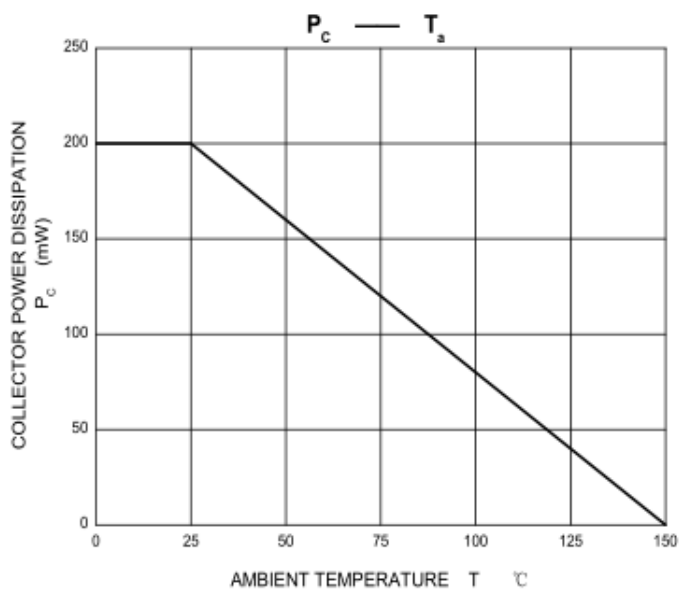
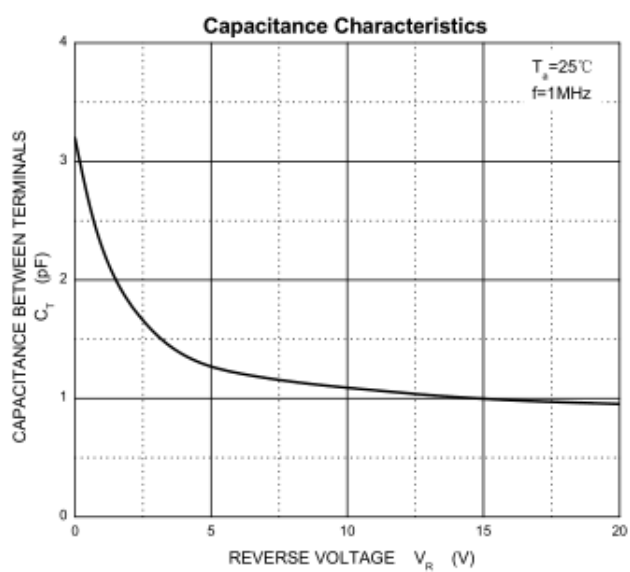
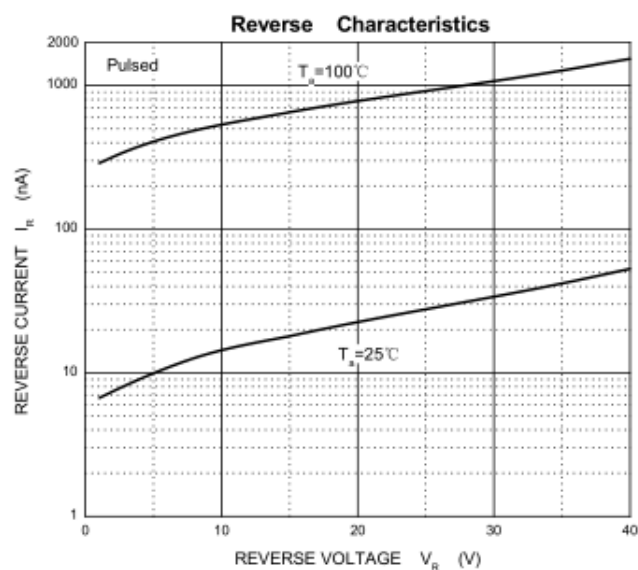
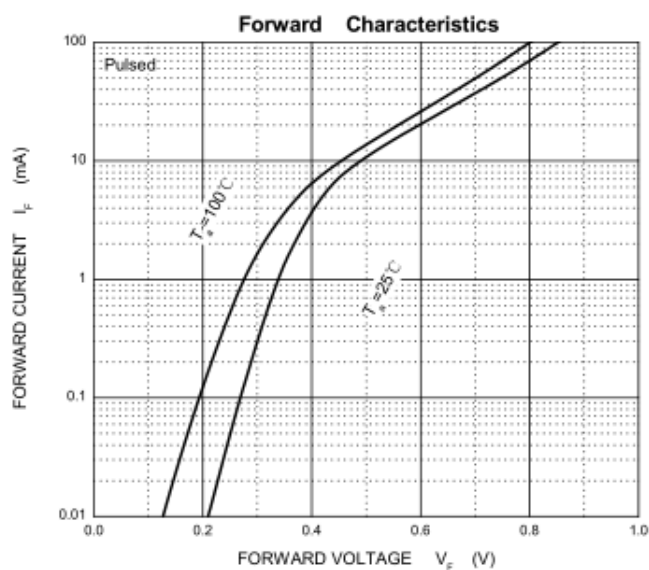
Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	Limits	Unit
Non-Repetitive Peak reverse voltage DC Blocking Voltage	V_{RM} V_R	40	V
Average Rectified Output Current	I_O	200	mA
Power Dissipation	P_d	200	mW
Thermal Resistance. Junction to Ambient Air	$R_{\theta JA}$	625	°C/W
Junction temperature	T_J	125	°C
Storage temperature range	T_{STG}	-65-125	°C

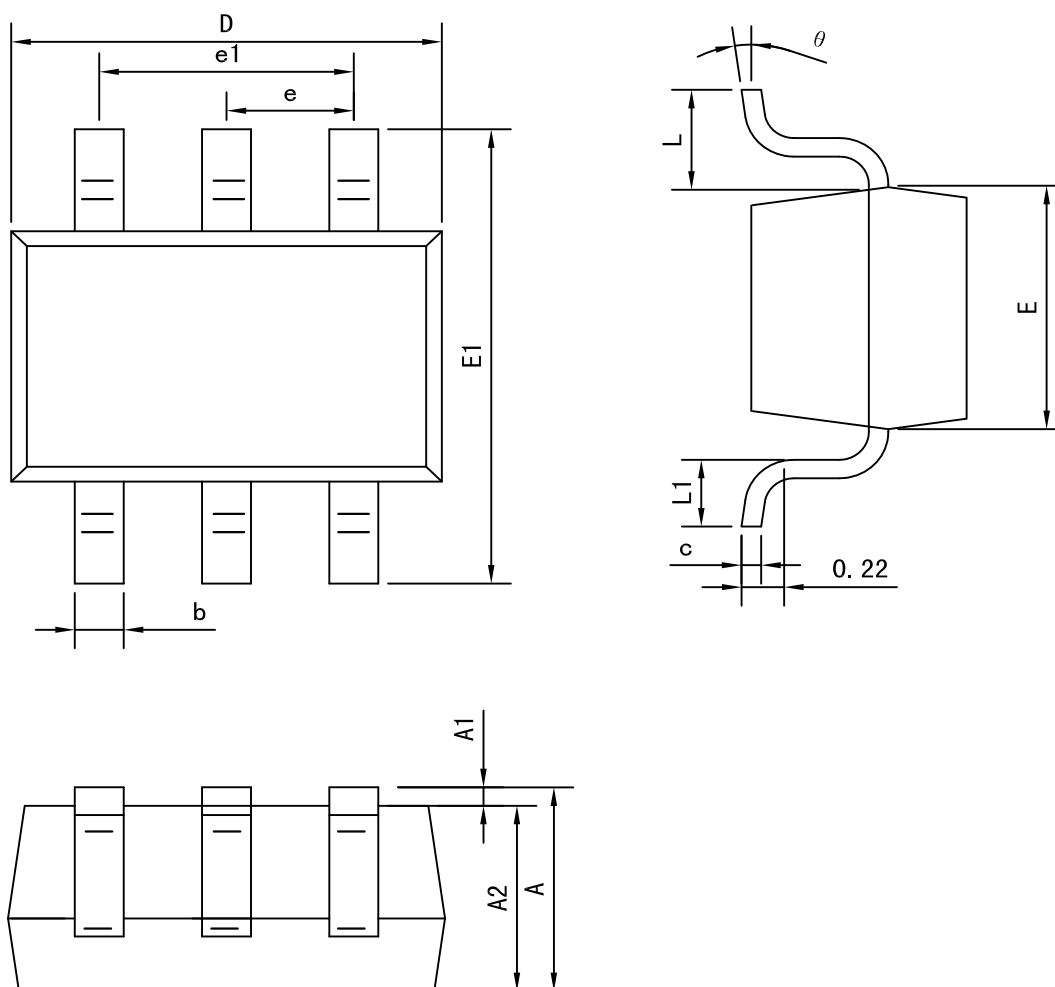
Electrical Ratings @Ta=25°C

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 10\mu A$	40		V
Reverse voltage leakage current	I_R	$V_R = 30V$		200	nA
Forward voltage	V_F	$I_F = 1mA$ $I_F = 40mA$		380 1000	mV
Total capacitance	C_T	$V_R = 0, f = 1MHz$		5	pF
Reverse recovery time	t_{rr}	$I_F = 10mA, I_R = I_F = 1mA$ $R_L = 100\Omega$		5	ns

Typical Characteristics



SOT-363 Package outline dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.150	0.350
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP	
e1	1.200	1.400
L	0.525 REF	
L1	0.260	0.460
θ	0°	8°